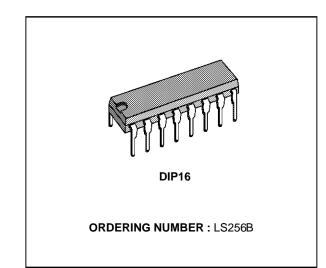


LS256

TELEPHONE SPEECH CIRCUIT WITH MULTIFREQUENCY TONE GENERATOR INTERFACE

- PRESENTS THE PROPER DC PATH FOR THE LINE CURRENT
- HANDLES THE VOICE SIGNAL, PERFORM-ING THE 2/4 WIRES INTERFACE AND CHANGING THE GAIN ON BOTH SENDING AND RECEIVING AMPLIFIERS TO COMPEN-SATE FOR LINE ATTENUATION BY SENSING THE LINE LENGTHTHROUGH THE LINE CUR-RENT
- ACTS AS LINEAR INTERFACE FOR MF, SUP-PLYING A STABILIZED TO THE DIGITAL CHIP AND DELIVERING TO THE LINE THE MF TONE GENERATED BY THE DIALER

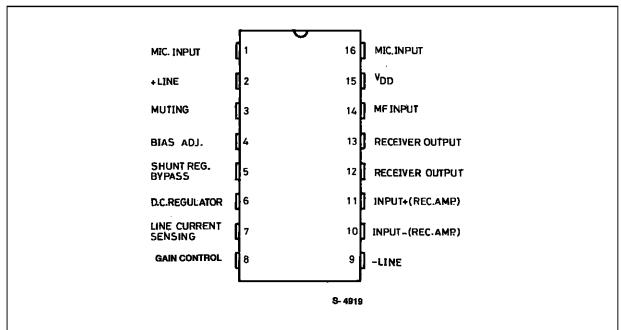


DESCRIPTION

The LS256 is a monolithic integrated circuit in 16lead dual in-line plastic package to replace the hybrid circuit in telephone set. It works with the same type of transdurcers for both transmitter and receiver (typically piezoceramic capsules, but the device can work also with dynamic ones). Many of its electrical characteristics can be controlled by means of external components to meet different specifications.

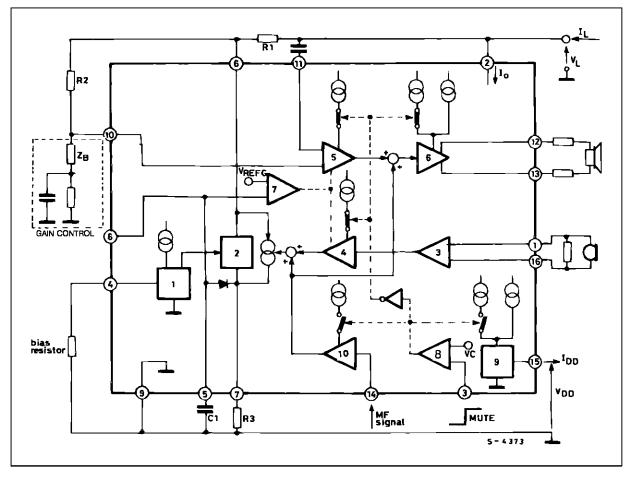
In addition to the speech operation, the LS256 acts as an interface for the MF tone signal.

PIN CONNECTION (top view)



LS256

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
VL	Line Voltage (3ms pulse duration)	22	V	
١L	Forward Line Current	150		
١L	Reverse Line Current	- 150		
P _{tot}	Total Power Dissipation at $T_{amb} = 70^{\circ}C$ 1		W	
T _{op}	Operating Temperature	– 45 to 70	°C	
T _{stg} , T _j	Storage and Junction Temperature - 65 to 150		°C	

THERMAL DATA

Symbol	Parameter		Unit
R _{th j-amb}	Thermal Resistance Junction-ambient Max	80	°C/W



TEST CIRCUITS

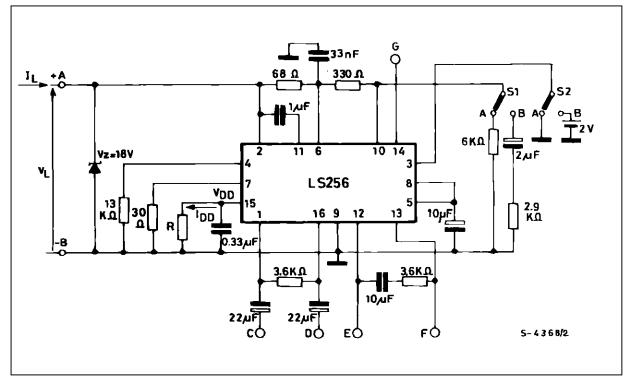
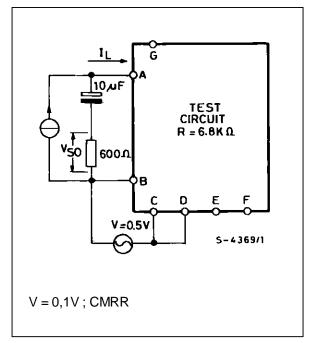
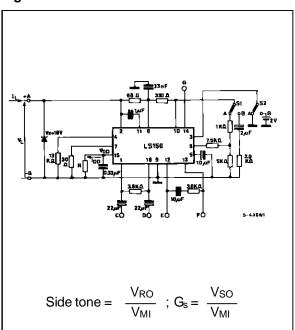
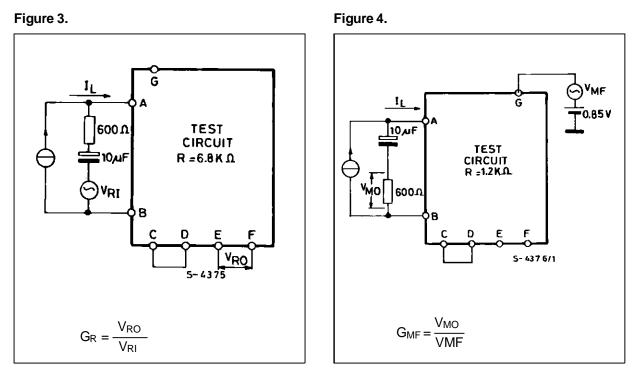


Figure 1.

Figure 2.







ELECTRICAL CHARACTERISTICS (refer to the test circuits, S1, S2 in (a),

 $T_{amb} = -25 \text{ to } + 50^{\circ}\text{C}$, f = 200 to 3400Hz, unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit	Fig.
SPEECH (OPERATION							
VL	Line Voltage	IL =	= 12mA = 20mA = 80mA	3.9		4.7 5.5 12.2	V	
CMRR	Common Mode Rejection	$f = 1$ kHz, $I_L = 12$ to 80mA		50			dB	1
Gs	Sending Gain	$\begin{array}{ll} T_{amb} = 25^{\circ}C, \ f = 1 \text{kHz} & I_L = \\ V_{MI} = 2mV & I_L = \end{array}$	= 52mA = 25mA	44 48	45 49	46 50	dB	2
	Sending Gain Flatness	$V_{MI} = 2mV, f_{ref} = 1kHz$ $I_L = 12 to 80mA$				± 1	dB	2
	Sending Distortion		o = 1V o = 1.3V			2 10	%	2
	Sending Noise	$V_{MI} = 0V; I_L = 40mA; S1 in$	(b)			-68.5	dBmp	2
	Microphone Input Impedance Pin 1-16	$V_{MI} = 2mV, I_L = 12 \text{ to } 80mA$	۱.	40			kΩ	
	Sending Loss in MF Operation		= 52mA = 25mA	- 30 - 30			dB	2
Gr	Receiving Gain		= 25°C = 52mA = 25mA	2.5 7	3.5 8	4.5 9	dB	3
	Receiving Gain Flatness	$\label{eq:VRI} \begin{array}{l} V_{\text{RI}} = 0.3 \text{V}, \ f_{\text{ref}} = 1 \text{kHz} \\ I_{\text{L}} = 12 \ \text{to} \ 80 \text{mA} \end{array}$				± 1	dB	3
	Receiving Distortion	$ \begin{array}{ll} f=1kHz & I_L=12mA & V_{RO} \\ I_L=12mA & V_{RO} \\ I_L=50mA & V_{RO} \\ I_L=50mA & V_{RO} \end{array} $	= 1.9V = 1.8V			2 10 2 10	%	3
	Receiving Noise	$V_{RI} = 0V; I_L = 12 \text{ to } 80\text{mA};$	S1 in (b)		100		μV	3
	Receiver Output Impedance Pin 12-13	$V_{RO} = 50 mV, I_{L} = 40 mA$				100	Ω	



ELECTRICAL CHARACTERISTICS (continued)

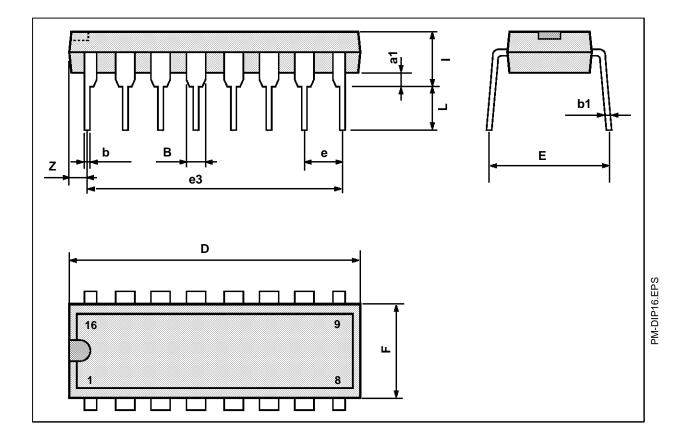
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	Fig.
SPEECH (DPERATION (continued)						
Gr	Sidetone	$\label{eq:F} \begin{array}{l} F = 1 \text{kHz}, \ T_{amb} = 25^\circ C, \ S1 \ \text{in} \ (b) \\ I_L = 52 \text{mA} \\ I_L = 25 \text{mA} \end{array}$			36 36	dB	2
Z _{ML}	Line Matching Impedance	$V_{RI} = 0.3V, f = 1kHz$ I _L = 12 to 80mA	500	600	700	Ω	
MULTIFRE	QUENCY SYNTHESIZER INTERF	ACE					
V _{DD}	MF Supply Voltage (standby and operation)	I _L = 12 to 80mA	2.4	2.5		V	
I _{DD}	MF Supply Current Stand by Operation	I_L = 12 to 80mA I_L = 12 to 80mA ; S ₂ in (b)	0.5 2			mA mA	
	MF Amplifier Gain	I_L = 12 to 80mA, f_{MF} in = 1kHz V_{MF} in = 80mV	15		17	dB	4
VI	DC Input Voltage Level (pin 14)	V _{M Fin} = 80mV		$3V_{DD}$		V	
Rı	Input Impedance (pin 14)	V _{M Fin} = 80mV	40			kΩ	
d	Distortion	$V_{M Fin} = 110mV$ I _L = 12 to 80mA			2	%	4
	Starting Delay Time	I _L = 12 to 80mA			5	ms	
	Muting Threshold Voltage (pin 3)	Speech Operation			1	V	
		MF Operation	1.6			V	
	Muting Stand by Current (pin 3)	I _L = 12 to 80mA			- 10	μA	
	Muting Operating Current (pin 3)	I _L = 12 to 80mA, S ₂ in (b)			+ 10	μA	



LS256

DIP16 PACKAGE MECHANICAL DATA

DIM.		mm			inch		7
	Min.	Тур.	Max.	Min.	Тур.	Max.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		L III.
е		2.54			0.100		DIP16.TBL
e3		17.78			0.700		75
F			7.1			0.280	
i			5.1			0.201	
L		3.3			0.130		7
Z			1.27			0.050	





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